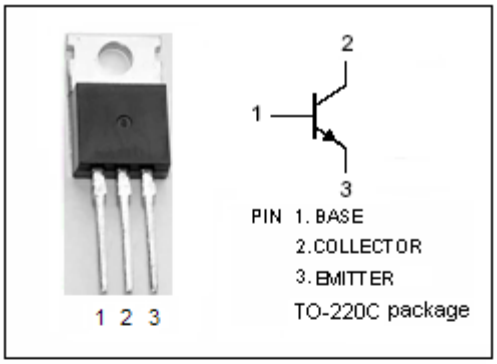
isc Silicon NPN Power Transistor BDY80

DESCRIPTION

- Continuous Collector Current-I_C= 4A
- Collector Power Dissipation-
  : P_C= 36W @T_C= 25℃
- Complement to Type BDY82



APPLICATIONS

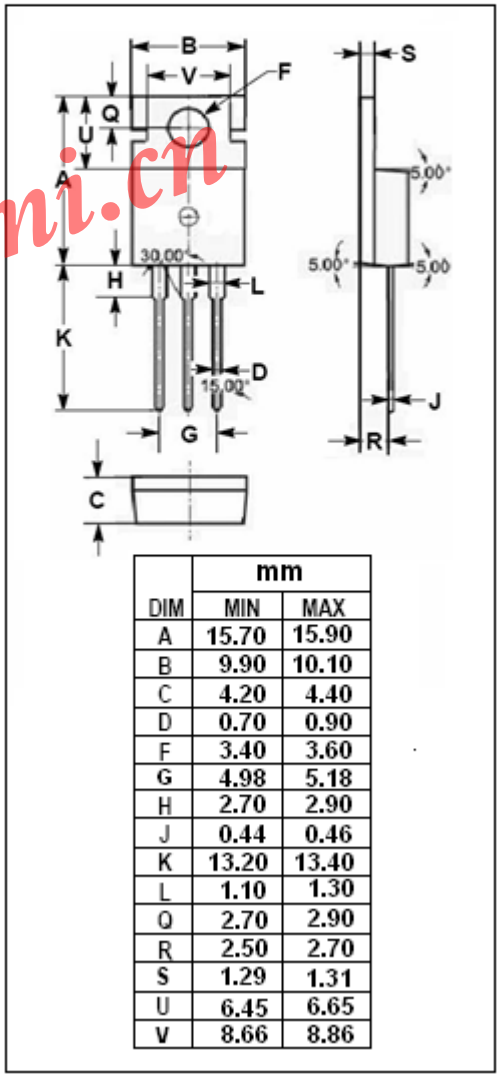
- Designed for general purpose switching and amplifier applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	40	V
V_{CEX}	Collector-Emitter Voltage V_{BE}= -1.5V	40	V
V_{CEO}	Collector-Emitter Voltage	35	V
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current-Continuous	4	A
I_B	Base Current-Continuous	2	A
P_C	Collector Power Dissipation@T_C=25℃	36	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~175	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	3.5	℃/W



DIM	mm MIN	MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 100mA; I_B= 0	35			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 10mA; I_E= 0	40			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 10mA; I_C= 0	10			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 1A; I_B= 0.05A			1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 0.5A; V_{CE}= 5V			0.9	V
I_{CEO}	Collector Cutoff Current	V_{CE}= 20V; I_B= 0			10	mA
I_{CBO}	Collector Cutoff Current	V_{CB}= 20V; I_E= 0			0.2	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			0.1	mA
h_{FE-1}	DC Current Gain	I_C= 0.5A; V_{CE}= 5V	40		240	
h_{FE-2}	DC Current Gain	I_C= 1A; V_{CE}= 5V	20			
f_T	Current Gain-Bandwidth Product	I_C= 0.5A; V_{CE}= 10V		1		MHz

◆ **h_{FE-1} Classifications**

A	B	C
40-80	70-140	120-240